

AMENDMENTS TO THE SPECIFICATION

On page 9, please amend paragraph [0031] as follows:

[0031] As shown in FIG. 5, the floating diffusion capacitor 82 is ~~formed over a portion of~~ coupled to the floating diffusion node 25, and is located between the transfer gate 50 and reset gate 40. The capacitor 82 covers an active area ~~that includes the floating diffusion node 25 of the pixel 210~~. The capacitor 82 can occupy a larger area compared to a transistor gate on a conventional pixel. The capacitor 82 needs only a source terminal as no drain terminal is necessary since the lower electrode of capacitor 82 is the floating diffusion node 25. Metal lines can be fabricated to connect with contact 83 which is electrically coupled to an upper electrode of capacitor 82. FIG. 5 also depicts a source follower gate 60 and row select gate 80 (described above with reference to FIG. 1).